

**Serial N . 09/588,351**  
**Art Unit: 2815**

### **REMARKS**

Applicant respectfully traverses the Examiner's withdrawal of claim 15. Nevertheless, Applicant cancelled claim 15 to facilitate examination of the instant application, provided that Applicant reserves its rights to represent claim 15 in this or another application.

#### **35 USC 102**

Applicant respectfully traverses the Examiner's rejections of claims 6-14.

Based upon information discovered to date, Applicant believes the earliest filing date to which 6,369,994 (Voldman) is entitled in July 31, 1998.

Applicant believes the instant application is a divisional application of 09/063,823 (filed 04/22/1998) which claims priority from provisional application serial no. 60/044,251 filed 04/23/1997.

Accordingly, Applicant believes Voldman is not prior art against the instant application.

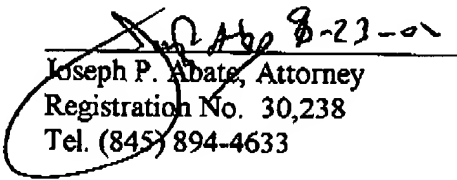
Reconsideration and allowance of claims 6-14 are solicited.

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Attached hereto is a marked-up version of the changes made to the claims by the current amendment. **This appendix is captioned "Version with Markings to Show Changes Made".**

Respectfully submitted,  
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Attachment: Appendix - Version with Markings to Show Changes Made

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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**In the Claims:**

**Kindly cancel claim 15:**

15. (Cancelled)[A method for reducing memory access time for a memory array which includes at least one SOI device, the method comprising:
- activating a memory segment driver;
  - selecting a memory segment in the memory array;
  - generating a pulse in response to said selecting a memory segment;
  - connecting a select line to a ground potential in response to the generated pulse;
  - discharging any accumulated charge from a body of the at least one SOI device to the ground potential; and
  - accessing the selected memory segment after said discharging step.]

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September 23, 2002